μPA2735GR

P-channel MOSFET
–30 V, –16 A, 5.0 mΩ

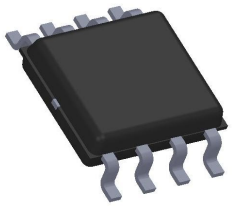
R07DS0867EJ0100
Rev.1.00
Aug 28, 2012

Description

The μPA2735GR is P-channel MOS Field Effect Transistor designed for DC/DC converter and power management applications of portable equipment.

Features

- V_{DSS} = –30 V (T_A = 25°C)
- Low on-state resistance
  — $R_{DS(on)}$ = 5.0 mΩ MAX. (V_{GS} = –10 V, I_D = –16 A)
- 4.5 V Gate-drive available
- Small and surface mount package (Power SOP8)
- Pb-free and Halogen free



Power SOP8

Ordering Information

Part No.	LEAD PLATING	PACKING	Package
μPA2735GR-E1-AT	Pure Sn	Tape 2500 p/reel	Power SOP8 0.08 g TYP.
μPA2735GR-E2-AT			

Absolute Maximum Ratings (T_A = 25°C)

Item	Symbol	Ratings	Unit
Drain to Source Voltage (V_{GS} = 0 V)	V_{DSS}	–30	V
Gate to Source Voltage (V_{DS} = 0 V)	V_{GSS}	∓20	V
Drain Current (DC)	$I_{D(DC)}$	∓16	A
Drain Current (pulse) *1	$I_{D(pulse)}$	∓150	A
Total Power Dissipation *2	P_{T1}	1.1	W
Total Power Dissipation (PW = 10 sec) *2	P_{T2}	2.5	W
Channel Temperature	T_{ch}	150	°C
Storage Temperature	T_{stg}	–55 to +150	°C
Single Avalanche Current *3	I_{AS}	16	A
Single Avalanche Energy *3	E_{AS}	25.6	mJ

Thermal Resistance

Channel to Ambient Thermal Resistance *2	$R_{th(ch-A)}$	114	°C/W

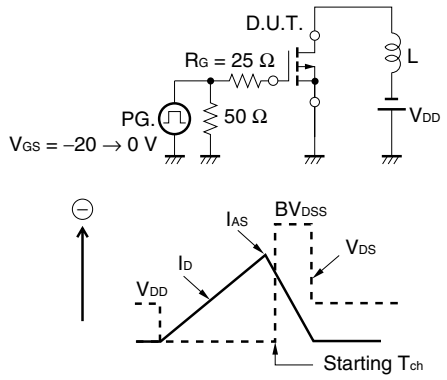
Notes: *1. PW ≤ 10 μs, Duty Cycle ≤ 1%
*2. Mounted on a glass epoxy board of 25.4 mm x 25.4 mm x 0.8 mmt
*3. Starting T_{ch} = 25°C, V_{DD} = –15 V, R_G = 25 Ω, V_{GS} = –20 → 0 V, L = 100 μH

Electrical Characteristics (T_A = 25°C)

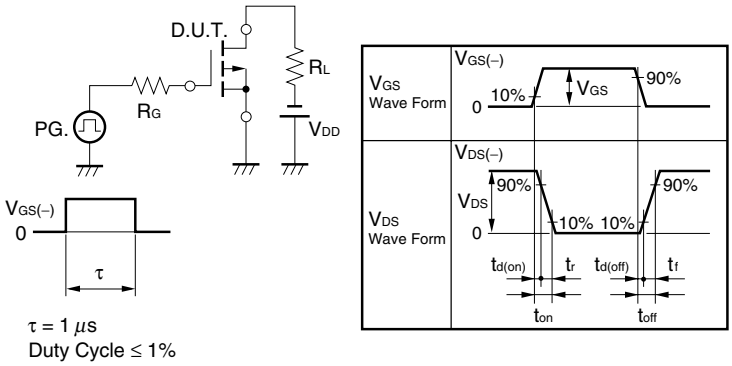
Item	Symbol	MIN.	TYP.	MAX.	Unit	Test Conditions
Zero Gate Voltage Drain Current	I_{DSS}			−1	μA	V_{DS} = −30 V, V_{GS} = 0 V
Gate Leakage Current	I_{GSS}			∓100	nA	V_{GS} = ∓20 V, V_{DS} = 0 V
Gate Cut-off Voltage	$V_{GS(off)}$	−1.0		−2.5	V	V_{DS} = −10 V, I_D = −1 mA
Forward Transfer Admittance *1	$\|y_{fs}\|$	10			S	V_{DS} = −10 V, I_D = −8.0 A
Drain to Source On-state Resistance *1	$R_{DS(on)1}$		3.8	5.0	mΩ	V_{GS} = −10 V, I_D = −16 A
	$R_{DS(on)2}$		5.1	7.8	mΩ	V_{GS} = −4.5 V, I_D = −16 A
Input Capacitance	C_{iss}		6250		pF	V_{DS} = −10 V,
Output Capacitance	C_{oss}		3900		pF	V_{GS} = 0 V,
Reverse Transfer Capacitance	C_{rss}		2850		pF	f = 1 MHz
Turn-on Delay Time	$t_{d(on)}$		35		ns	V_{DD} = −15 V, I_D = −8.0 A,
Rise Time	t_r		85		ns	V_{GS} = −10 V,
Turn-off Delay Time	$t_{d(off)}$		300		ns	R_G = 10 Ω
Fall Time	t_f		400		ns	
Total Gate Charge	Q_G		195		nC	V_{DD} = −24 V,
Gate to Source Charge	Q_{GS}		15		nC	V_{GS} = −10 V,
Gate to Drain Charge	Q_{GD}		100		nC	I_D = −16 A
Body Diode Forward Voltage *1	$V_{F(S-D)}$		0.82		V	I_F = 16 A, V_{GS} = 0 V
Reverse Recovery Time	t_{rr}		60		ns	I_F = 16 A, V_{GS} = 0 V,
Reverse Recovery Charge	Q_{rr}		88		nC	di/dt = 100 A/μs

Note: *1. Pulsed

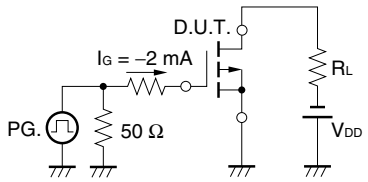
TEST CIRCUIT 1 AVALANCHE CAPABILITY



TEST CIRCUIT 2 SWITCHING TIME

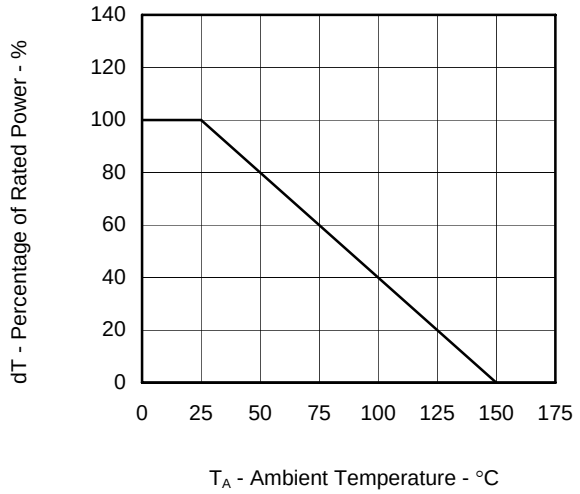


TEST CIRCUIT 3 GATE CHARGE

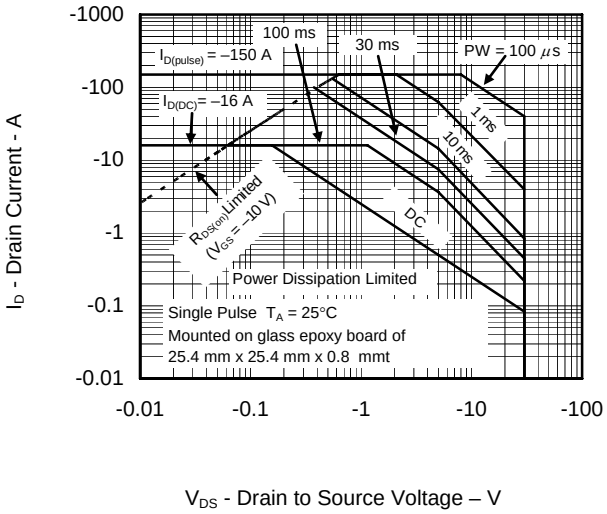


TYPICAL CHARACTERISTICS (T_A = 25°C)

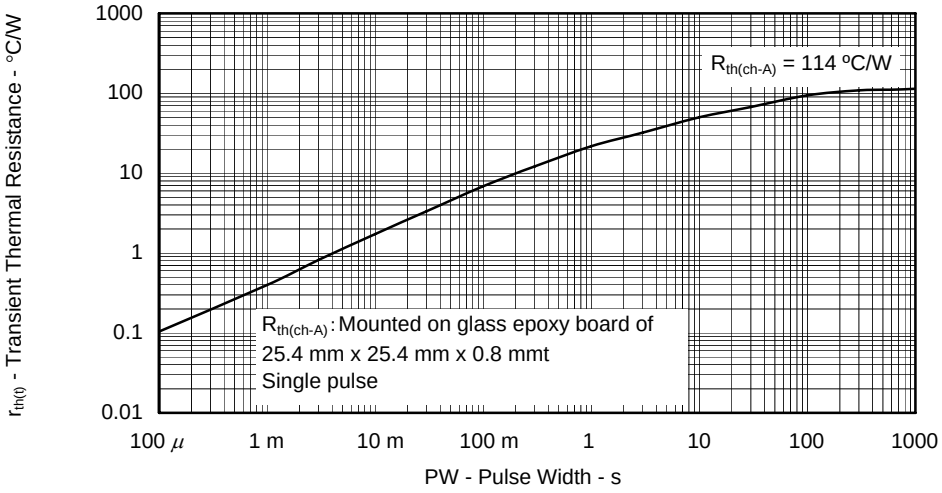
DERATING FACTOR OF FORWARD BIAS SAFE OPERATING AREA



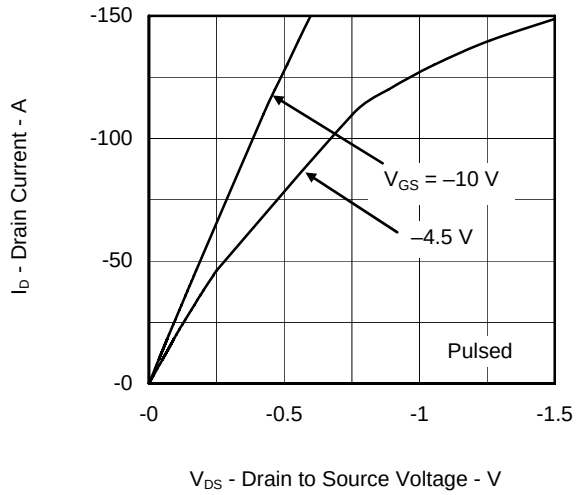
FORWARD BIAS SAFE OPERATING AREA



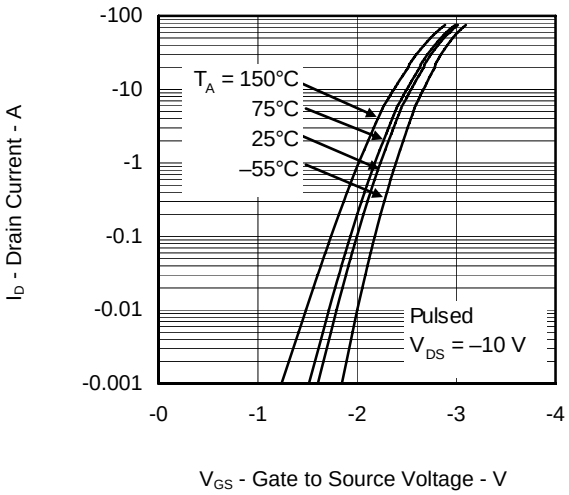
TRANSIENT THERMAL RESISTANCE vs. PULSE WIDTH



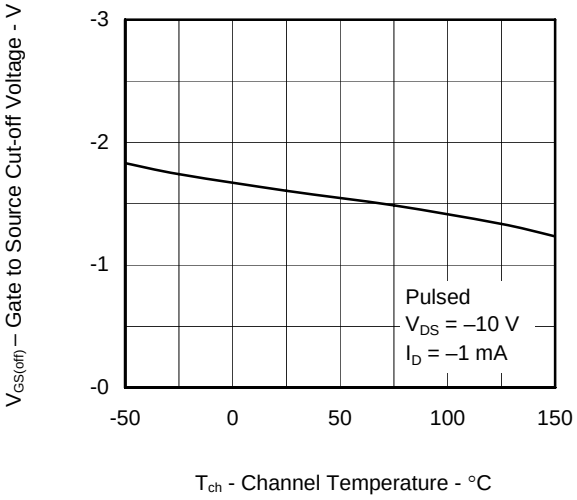
DRAIN CURRENT vs. DRAIN TO SOURCE VOLTAGE



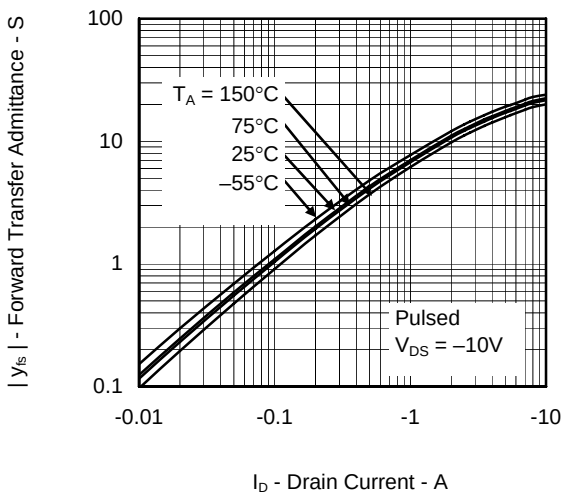
FORWARD TRANSFER CHARACTERISTICS



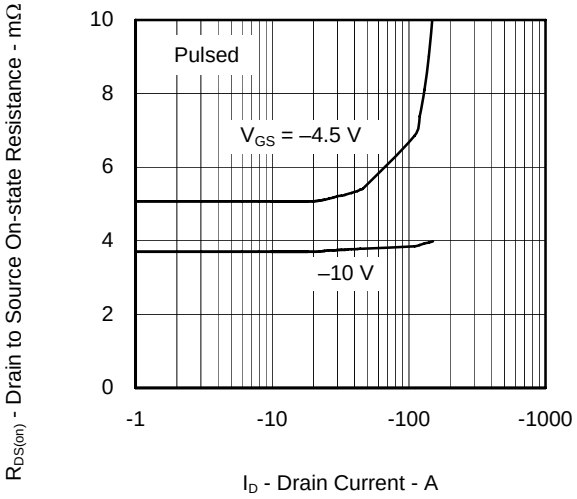
GATE TO SOURCE CUT-OFF VOLTAGE vs. CHANNEL TEMPERATURE



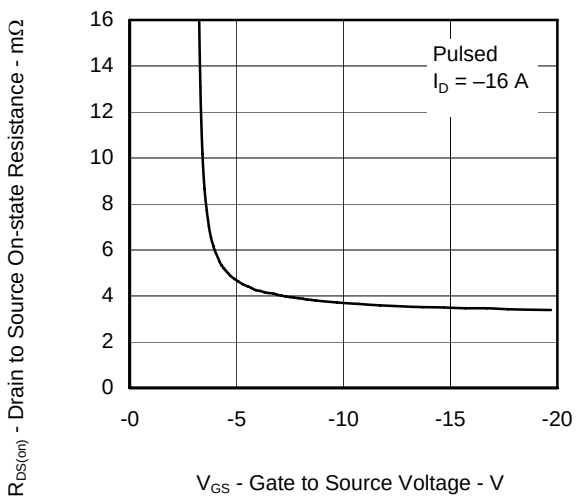
FORWARD TRANSFER ADMITTANCE vs. DRAIN CURRENT



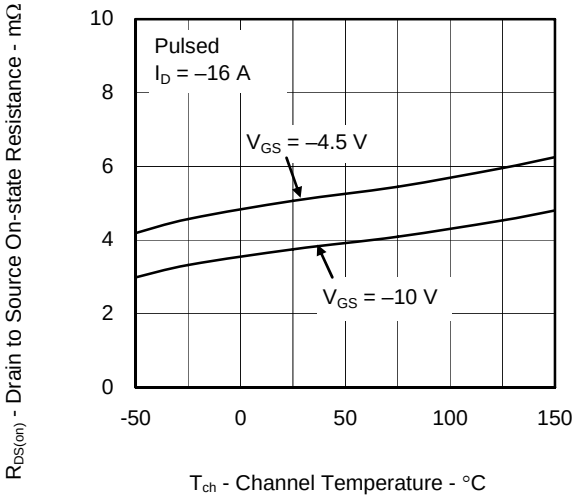
DRAIN TO SOURCE ON-STATE RESISTANCE vs. DRAIN CURRENT



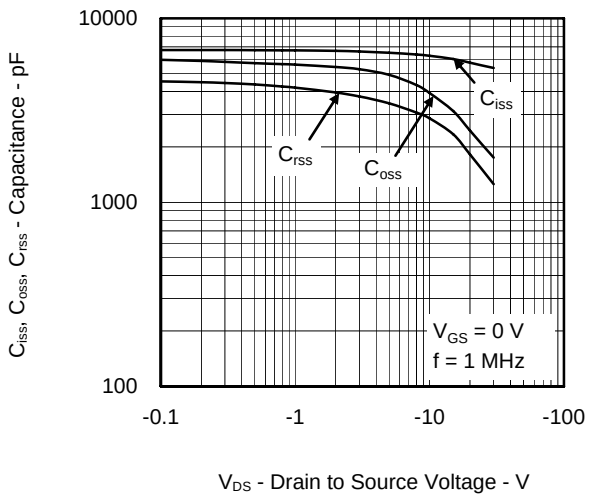
DRAIN TO SOURCE ON-STATE RESISTANCE vs. GATE TO SOURCE VOLTAGE



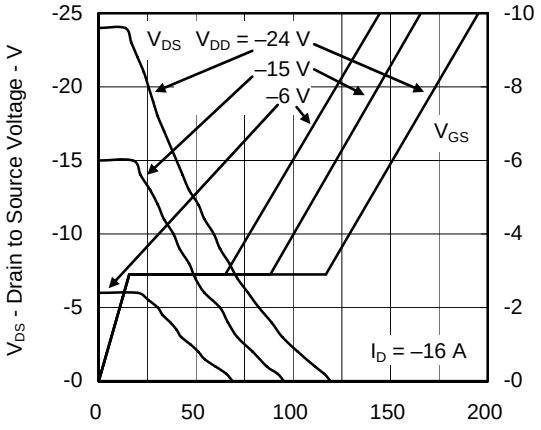
DRAIN TO SOURCE ON-STATE RESISTANCE vs. CHANNEL TEMPERATURE



CAPACITANCE vs. DRAIN TO SOURCE VOLTAGE

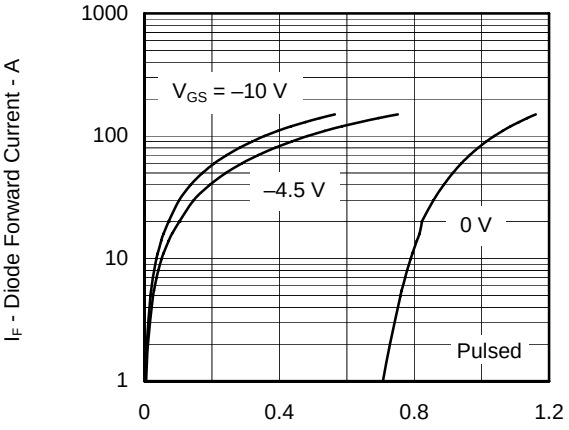


DYNAMIC INPUT/OUTPUT CHARACTERISTICS



Q_G - Gate Charge - nC

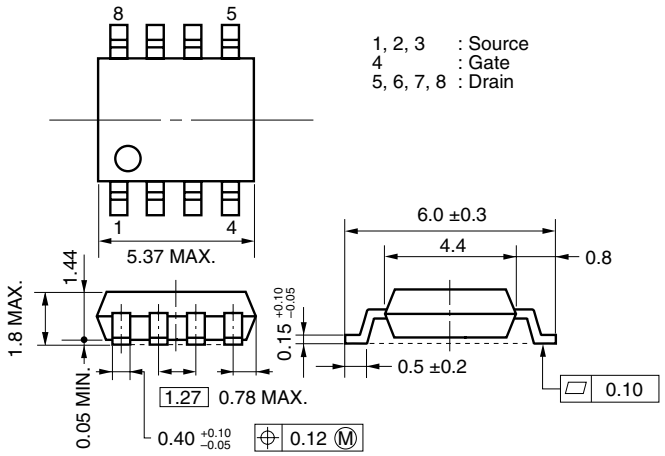
SOURCE TO DRAIN DIODE FORWARD VOLTAGE



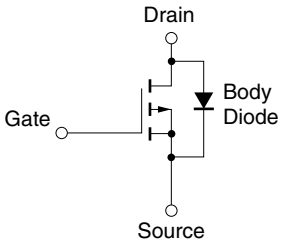
$V_{F(S-D)}$ - Source to Drain Voltage - V

Package Drawings (Unit: mm)

Power SOP8



Equivalent Circuit



Remark Strong electric field, when exposed to this device, can cause destruction of the gate oxide and ultimately degrade the device operation. Steps must be taken to stop generation of static electricity as much as possible, and quickly dissipate it once, when it has occurred.

Revision History	μPA2735GR Data Sheet

Rev.	Date	Description	
		Page	Summary
1.00	Aug 28, 2012	–	First Edition Issued

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